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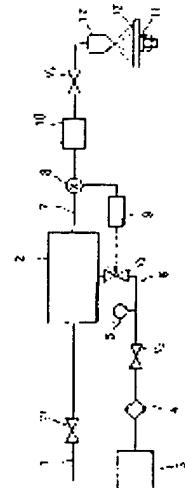
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(54) SUBSTRATE CLEANING

(57) Abstract:

PURPOSE: To control the resistivity of pure water at a low value and to prevent the generation of static electricity at the surface of a wafer by using cleaning liquid wherein ozone is dissolved into the pure water when a semiconductor substrate is cleaned with the pure water.

CONSTITUTION: A super-pure-water feeding pipe 1 is connected to a dissolver 2 through a flow-rate regulating valve V1. Particles in ozone which is generated in an ozone generator 3 are removed through a filter 4. The feeding amount is regulated through a flow-rate regulating valve V2. Thus, the ozone is kept within a specified pressure range. The specified amount of ozone is supplied into the dissolver 2 for a specified time period. The resistivity value of the super-pure water for cleaning is measured with a resistivity meter 8. When the resistivity value within the specified value range is obtained, a wafer 12 which is a body to be treated is mounted on a chuck 11 and turned at a high speed. At the same time, a pressure regulating device 10 is actuated, and the pressure of the cleaning water is made high. The cleaning water is jetted through a jetting nozzle 13, and the cleaning is performed.



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